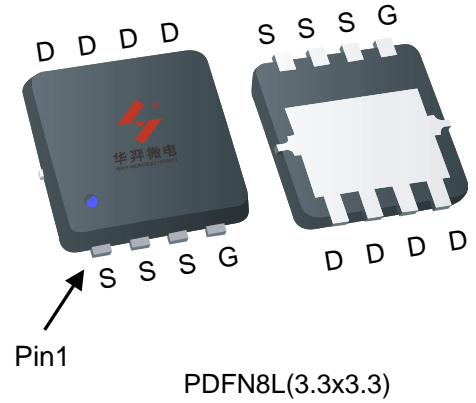


N-Channel Enhancement Mode MOSFET

Feature

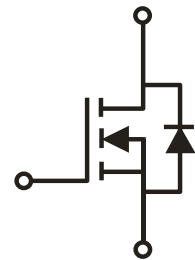
- 60V/55A
R_{DS(ON)} = 8.2 mΩ(typ.) @VGS = 10V
- 100% Avalanche Tested
- 100% DVDS
- Reliable and Rugged
- Halogen Free and Green Devices Available
(RoHS Compliant)

Pin Description




Applications

- Switching application
- Li-battery protection
- Power Management for DC/DC



Single N-Channel MOSFET

Ordering and Marking Information

 <p style="margin: 0;">C1 HYG092N06 XYMXXXXXX</p>	<p>Package Code C1: PDFN8L(3.3x3.3)</p> <p>Date Code XYMXXXXXX</p>
--	--

Note: HUAYI halogen free products contain molding compounds/die attach materials and 100% matte tin plate Termination finish; which are fully compliant with RoHS. HUAYI halogen free products meet or exceed the halogen free requirements of IPC/JEDEC J-STD-020 for MSL classification at halogen free peak reflow temperature. HUAYI defines “Green” to mean halogen free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage	60	V	
V _{GSS}	Gate-Source Voltage	± 20	V	
T _J	Junction Temperature Range	-55 to 175	°C	
T _{STG}	Storage Temperature Range		°C	
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	55	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	160	A
I _D	Continuous Drain Current	Tc=25°C	55	A
		Tc=100°C	38.9	A
P _D	Maximum Power Dissipation	Tc=25°C	58.8	W

Electrical Characteristics (Cont.) (T_c =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG092N06LS1			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	0.9	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, Frequency=1MHz	-	1020	-	pF
C _{oss}	Output Capacitance					
C _{rss}	Reverse Transfer Capacitance					
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _G =4Ω, I _{DS} =20A, V _{GS} =10V	-	8.7	-	ns
T _r	Turn-on Rise Time					
t _{d(OFF)}	Turn-off Delay Time					
T _f	Turn-off Fall Time					
Gate Charge Characteristics						
Q _g	Total Gate Charge(V _{GS} =10V)	V _{DS} =48V, I _{DS} =20A	-	18	-	nC
Q _{gs}	Gate-Source Charge					
Q _{gd}	Gate-Drain Charge					
V _{plateau}	Gate plateau voltage		-	4.2	-	V

Note: *Pulse test pulse width ≤ 300us duty cycle ≤ 2%

Typical Operating Characteristics

Figure 1: Power Dissipation

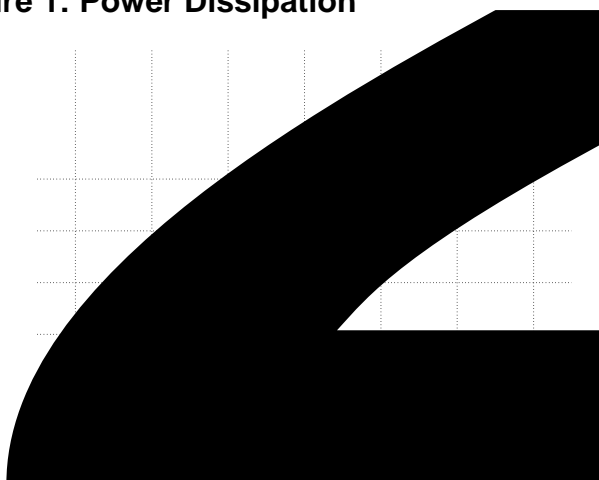


Figure 2: Drain Current

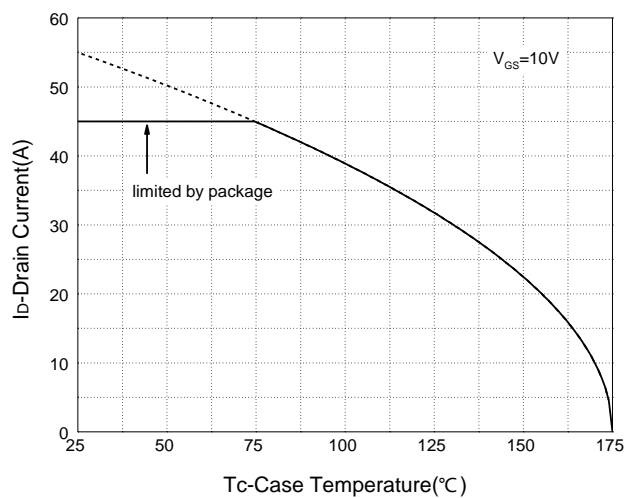


Figure 3: Safe Operation Area

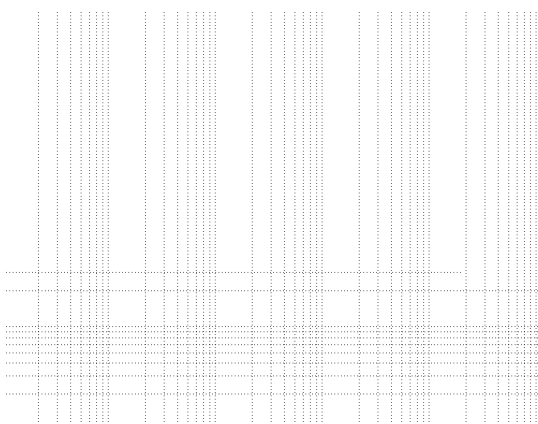


Figure 4: Thermal Transient Impedance

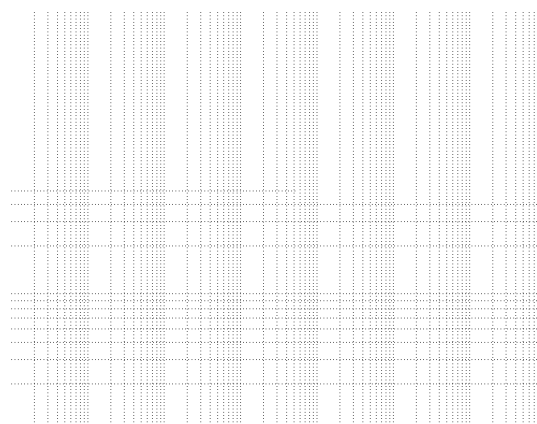


Figure 5: Output Characteristics

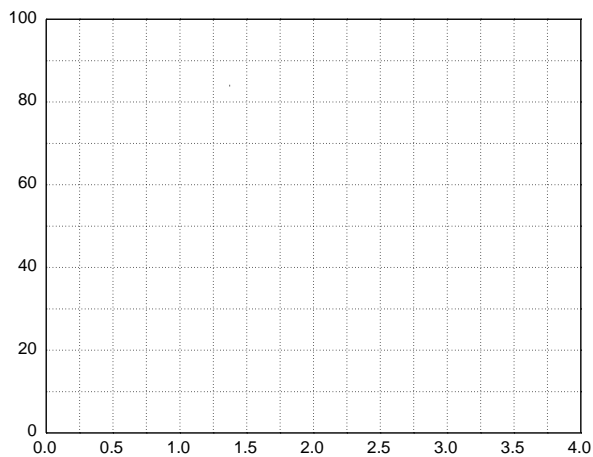
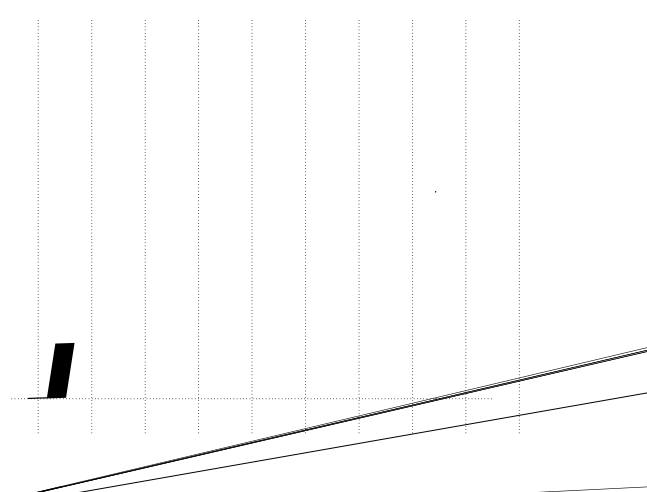


Figure 6: Drain-Source On Resistance



Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

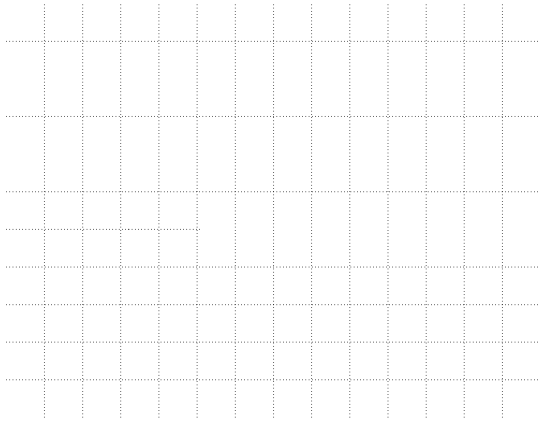


Figure 8: Source-Drain Diode Forward

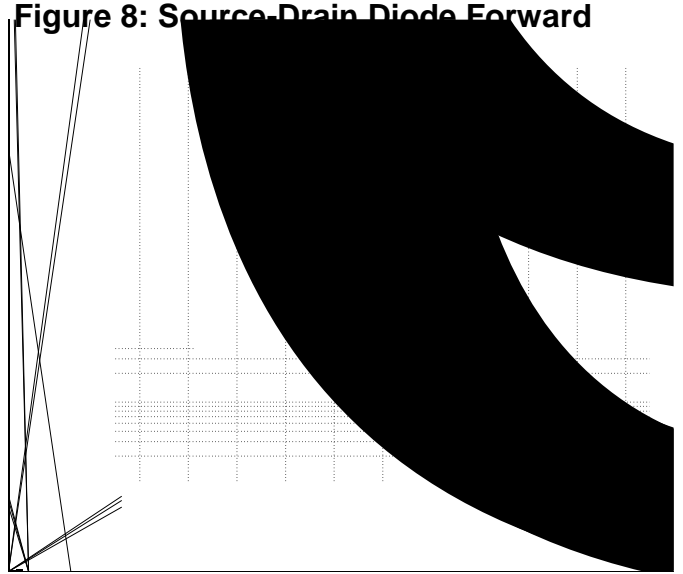


Figure 9: Capacitance Characteristics

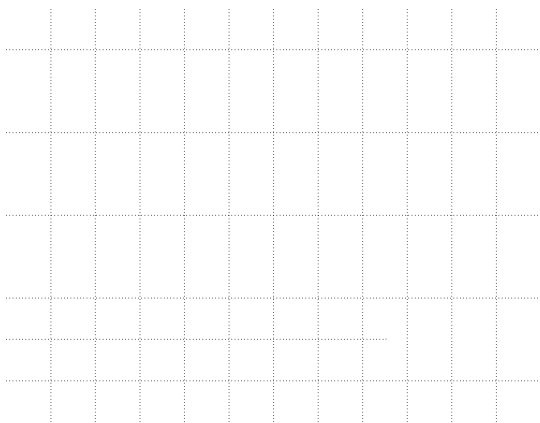
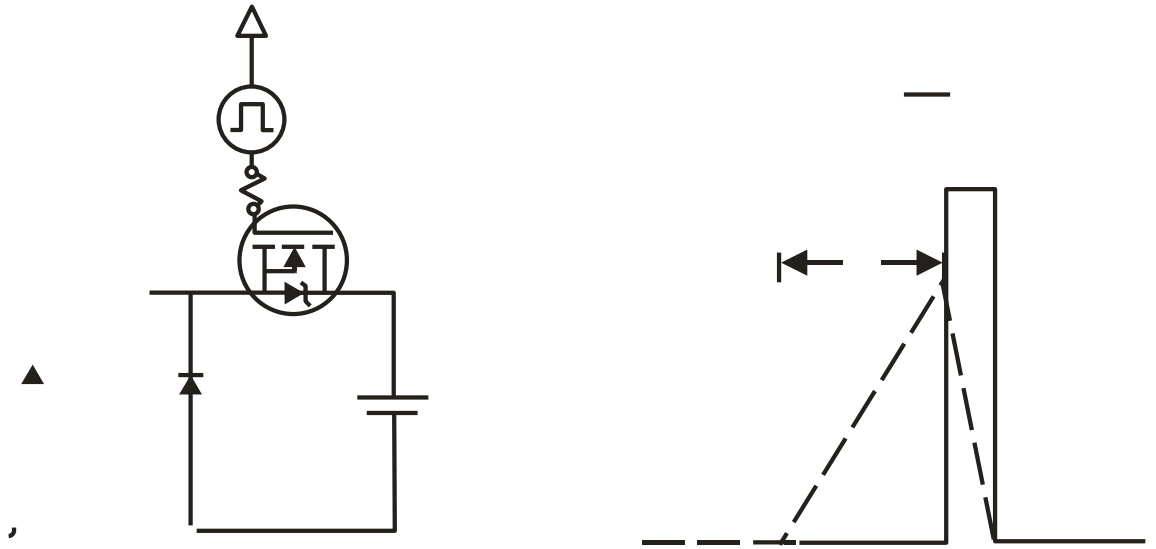


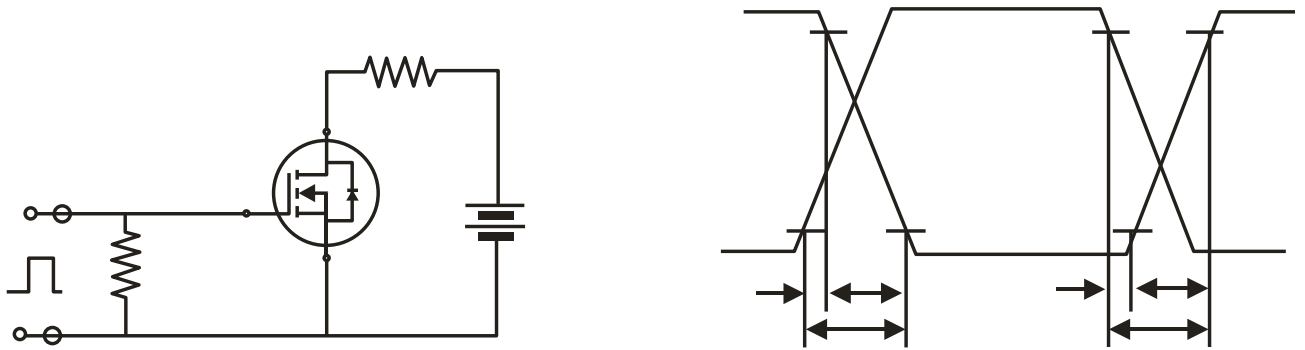
Figure 10: Gate Charge Characteristics



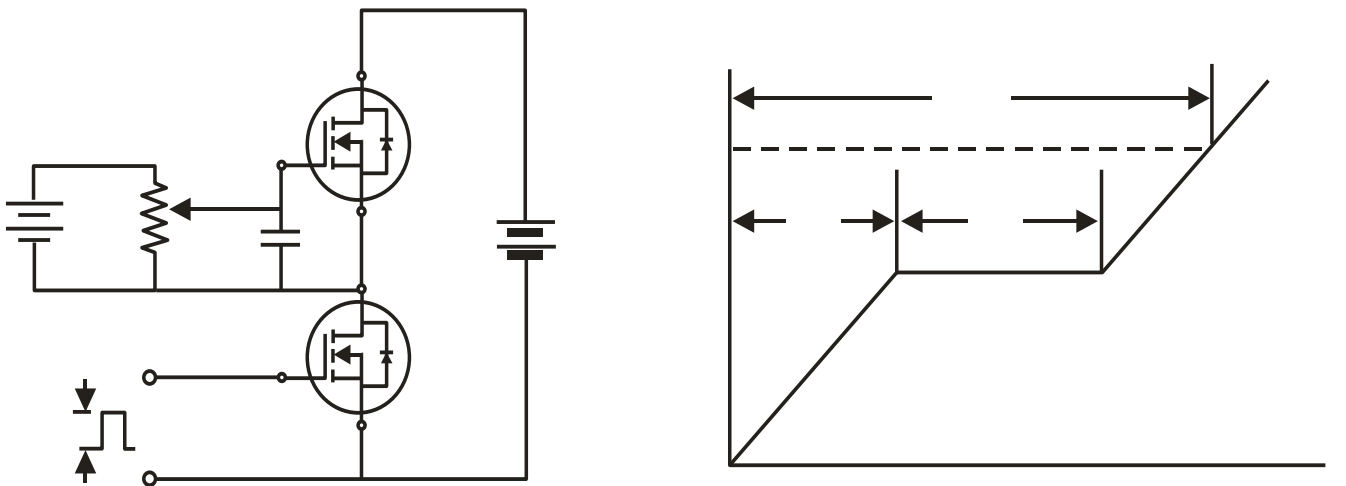
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit



Device Per Unit

Package Type	Unit	Quantity
PDFN8L(3.3x3.3)	Reel	6500

Package Information

PDFN8L(3.3x3.3)

COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
E1	3.10	3.20	3.30
E2	2.44	2.54	2.64
e	0.65BSC		
H	0.30		

Classification Profile

Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds

Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350
2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ 2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168/500 Hrs, Bias @ 150°C
HTGB	JESD-22, A108	168 /500 Hrs, V _{gs} 100% @ 150°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	250/500 Cycles, -55°C~150°C

Customer Service

Worldwide Sales and Service: sales@hymexa.com

Technical Support: Technology@hymexa.com

Huayi Microelectronics Co., Ltd.

No.8928, Shangji Road, Economic and Technological Development Zone, Xi'an, China

TEL: (86-029) 86685706

FAX: (86-029) 86685705

E-mail: sales@hymexa.com

Web net: <http://www.hymexa.com/>